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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SAI, SPDIF, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f765vgt6tr

1 Description

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices are based on the high-performance ARM® Cortex®-M7 32-bit RISC core operating at up to 216 MHz frequency. The Cortex®-M7 core features a floating point unit (FPU) which supports ARM® double-precision and single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances the application security.

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices incorporate high-speed embedded memories with a Flash memory up to 2 Mbytes, 512 Kbytes of SRAM (including 128 Kbytes of Data TCM RAM for critical real-time data), 16 Kbytes of instruction TCM RAM (for critical real-time routines), 4 Kbytes of backup SRAM available in the lowest power modes, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses, a 32-bit multi-AHB bus matrix and a multi layer AXI interconnect supporting internal and external memories access.

All the devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers, a true random number generator (RNG). They also feature standard and advanced communication interfaces.

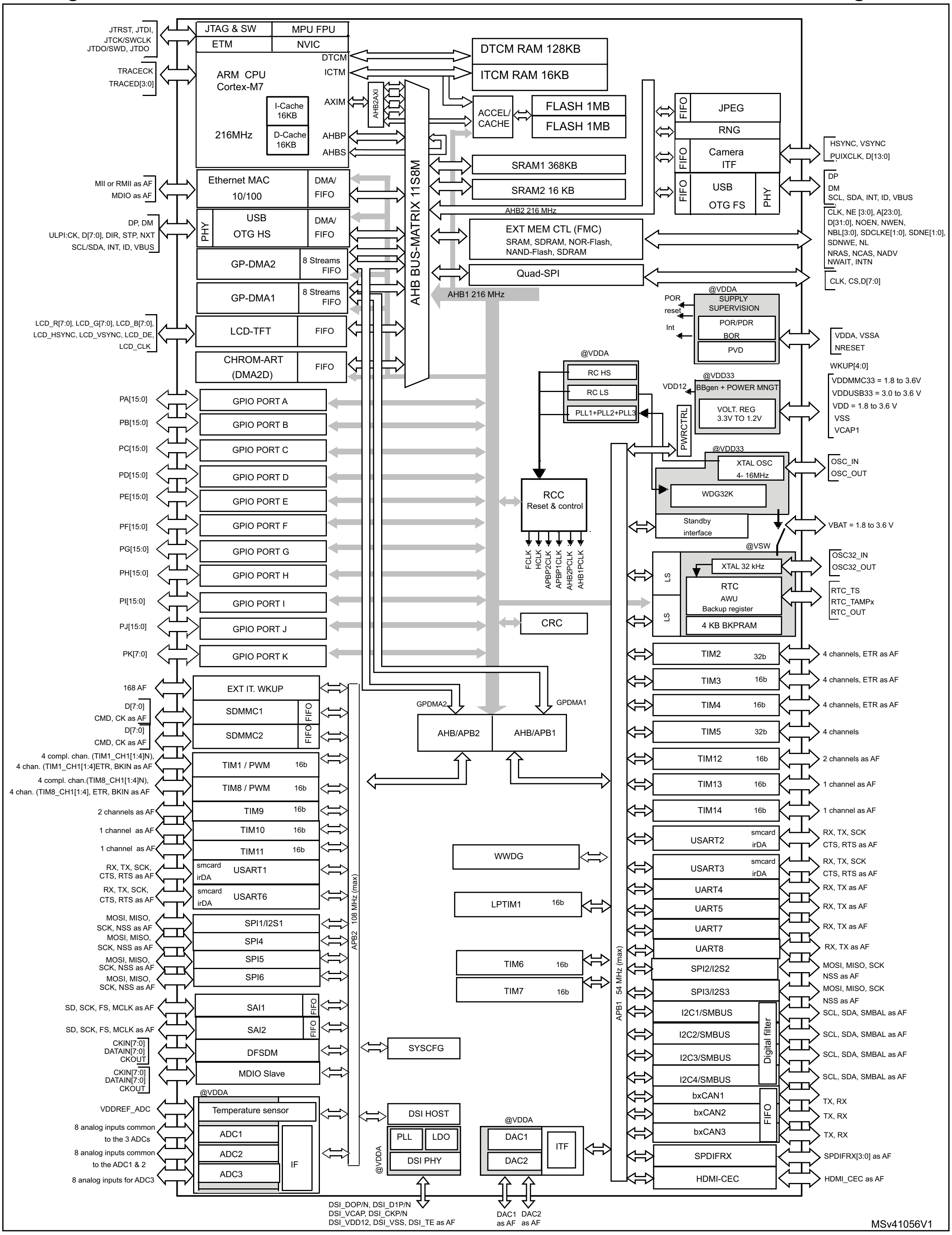
- Up to four I^2Cs
- Six SPIs, three I^2Ss in half-duplex mode. To achieve audio class accuracy, the I^2S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus four UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI)
- Three CANs
- Two SAI serial audio interfaces
- Two SDMMC host interfaces
- Ethernet and camera interfaces
- LCD-TFT display controller
- Chrom-ART Accelerator™
- SPDIFRX interface
- HDMI-CEC

Advanced peripherals include two SDMMC interfaces, a flexible memory control (FMC) interface, a Quad-SPI Flash memory interface, a camera interface for CMOS sensors. Refer to *Table 2: STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and peripheral counts* for the list of peripherals available on each part number.

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices operate in the –40 to +105 °C temperature range from a 1.7 to 3.6 V power supply. Dedicated supply inputs for USB (OTG_FS and OTG_HS) and SDMMC2 (clock, command and 4-bit data) are available on all the packages except LQFP100 for a greater power supply choice.

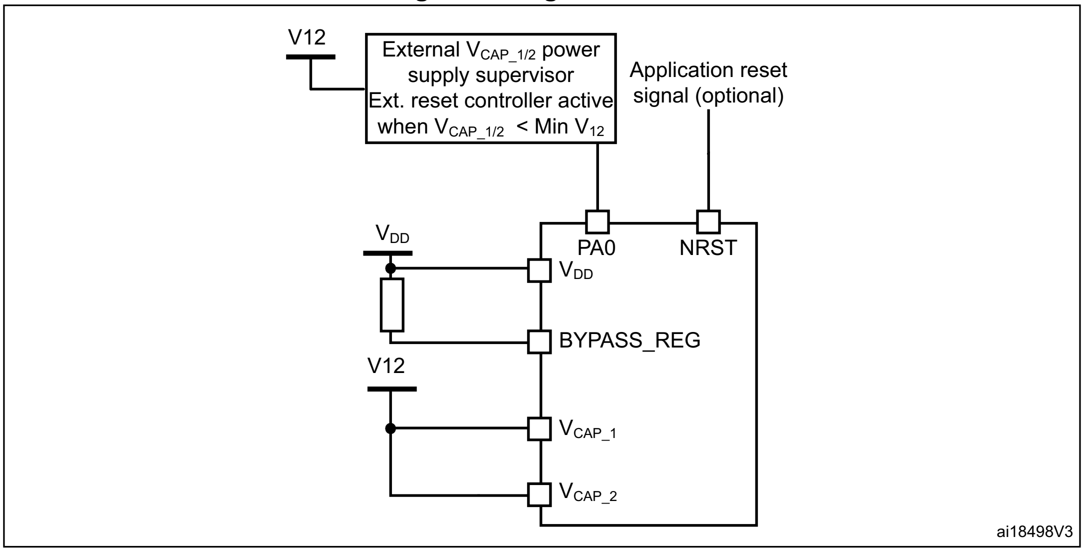
The supply voltage can drop to 1.7 V with the use of an external power supply supervisor (refer to *Section 2.18.2: Internal reset OFF*). A comprehensive set of power-saving mode allows the design of low-power applications.

Figure 2. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx block diagram



1. The timers connected to APB2 are clocked from TIMxCLK up to 216 MHz, while the timers connected to APB1 are clocked from TIMxCLK either up to 108 MHz or 216 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.

Figure 8. Regulator OFF



The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see *Figure 9*).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see *Figure 10*).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application.

- 16-bit RGB, configurations 1, 2, and 3
- 18-bit RGB, configurations 1 and 2
- 24-bit RGB

- Programmable polarity of all LTDC interface signals
- Extended resolutions beyond the DPI standard
- Maximum resolution of 800x480 pixels:
- Maximum resolution is limited by available DSI physical link bandwidth:
  - Number of lanes: 2
  - Maximum speed per lane: 500 Mbps1Gbps

Adapted interface features

Support for sending large amounts of data through the memory_write_start(WMS) and memory_write_continue(WMC) DCS commands

- LTDC interface color coding mappings into 24-bit interface:
  - 16-bit RGB, configurations 1, 2, and 3
  - 18-bit RGB, configurations 1 and 2
  - 24-bit RGB

Video mode pattern generator:

- Vertical and horizontal color bar generation without LTDC stimuli
- BER pattern without LTDC stimuli

Figure 20. STM32F769xx TFBGA216 ballout

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
A	PE4	PE3	PE2	PG14	PE1	PE0	PB8	PB5	PB4	PB3	PD7	PC12	PA15	PA14	PA13
B	PE5	PE6	PG13	PB9	PB7	PB6	PG15	PG11	PJ13	PJ12	PD6	PD0	PC11	PC10	PA12
C	VBAT	PI8	PI4	PK7	PK6	PK5	PG12	PG10	PJ14	PD5	PD3	PD1	PI3	PI2	PA11
D	PC13	PF0	PI5	PI7	PI10	PI6	PK4	PK3	PG9	PJ15	PD4	PD2	PH15	PI1	PA10
E	PC14	PF1	PI12	PI9	PDR_ON	BOOT0	VDD	VDD	VDD SDMMC	VDD	VCAP2	PH13	PH14	PI0	PA9
F	PC15	VSS	PI11	VDD	VDD	VSS	VSS	VSS	VSS	VSS	VDD	DSI_D1P	DSI_D1N	PC9	PA8
G	PH0	PF2	PI13	PI15	VDD	VSS				VSS	VDDUSB	VSSDSI	VDD12 DSI	PC8	PC7
H	PH1	PF3	PI14	PH4	VDD	VSS				VSS	VDDDSI	DSI_CKP	DSI_CKN	PG8	PC6
J	NRST	PF4	PH5	PH3	VDD	VSS				VSS	VDD	DSI_D0P	DSI_D0N	PG7	PG6
K	PF7	PF6	PF5	PH2	VDD	VSS	VSS	VSS	VSS	VSS	VDD	VCAPDSI	PD15	PB13	PD10
L	PF10	PF9	PF8	PC3	BYPASS-REG	VSS	VDD	VDD	VDD	VDD	VCAP1	PD14	PB12	PD9	PD8
M	VSSA	PC0	PC1	PC2	PB2	PF12	PG1	PF15	PJ4	PD12	PD13	PG3	PG2	PJ5	PH12
N	VREF-	PA1	PA0	PA4	PC4	PF13	PG0	PJ3	PE8	PD11	PG5	PG4	PH7	PH9	PH11
P	VREF+	PA2	PA6	PA5	PC5	PF14	PJ2	PF11	PE9	PE11	PE14	PB10	PH6	PH8	PH10
R	VDDA	PA3	PA7	PB1	PB0	PJ0	PJ1	PE7	PE10	PE12	PE15	PE13	PB11	PB14	PB15

MS39125V1

1. The above figure shows the package top view.

Table 9. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O directly connected to ADC
	B	Dedicated BOOT pin
	RST	Bidirectional reset pin with weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

Table 10. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions

Pin Number										Pin name (function after reset	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F765xx STM32F767xx						STM32F768Ax STM32F769xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180(1)	LQFP176	LQFP208	TFBGA216						
1	1	A2	1	1	A3	E10	1	1	A3	PE2	I/O	FT	-	TRACECLK, SPI4_SCK, SAI1_MCLK_A, QUADSPI_BK1_IO2, ETH_MII_TXD3, FMC_A23, EVENTOUT	-
2	2	A1	2	2	A2	F10	2	2	A2	PE3	I/O	FT	-	TRACED0, SAI1_SD_B, FMC_A19, EVENTOUT	-

Table 12. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	I2C4/UART5/TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/DFSDM1/CEC	I2C1/2/3/4/USART1/CEC	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5/6	SPI2/I2S2/SPI3/I2S3/SAI1/I2C4/UART4/DFSDM1	SPI2/I2S2/SPI3/I2S3/SPI6/USART1/2/3/UART5/DFSDM1/SPDIF	SPI6/SAI2/USART6/UART4/5/7/8/OTG_FS/SPDIF	CAN1/2/TIM12/13/14/QUADSPI/FMC/LCD	SAI2/QUADSPI/SDMMC2/DFSDM1/OTG2_HS/OTG1_FS/LCD	I2C4/CAN3/SDMMC2/ETH	UART7/FMC/SDMMC1/MDIOS/OTG2_FS	DCMI/LCD/DSI	LCD	SYS
Port C	PC0	-	-	-	DFSDM1_CKIN0	-	-	DFSDM1_DATIN4	-	SAI2_FS_B	-	OTG_HS_ULPI_STP	-	FMC_SDNWE	-	LCD_R5	EVENTOUT
	PC1	TRACED0	-	-	DFSDM1_DATAIN0	-	SPI2_MOSI/I2S2_SD	SAI1_SD_A	-	-	-	DFSDM1_CKIN4	ETH_MDC	MDIOS_MDC	-	-	EVENTOUT
	PC2	-	-	-	DFSDM1_CKIN1	-	SPI2_MISO	DFSDM1_CKOUT	-	-	-	OTG_HS_ULPI_DIR	ETH_MII_TXD2	FMC_SDNE0	-	-	EVENTOUT
	PC3	-	-	-	DFSDM1_DATAIN1	-	SPI2_MOSI/I2S2_SD	-	-	-	-	OTG_HS_ULPI_NXT	ETH_MII_TX_CLK	FMC_SDCKE0	-	-	EVENTOUT
	PC4	-	-	-	DFSDM1_CKIN2	-	I2S1_MCK	-	-	SPDIF_RX2	-	-	ETH_MII_RXD0/ETH_RMII_RXD0	FMC_SDNE0	-	-	EVENTOUT
	PC5	-	-	-	DFSDM1_DATAIN2	-	-	-	-	SPDIF_RX3	-	-	ETH_MII_RXD1/ETH_RMII_RXD1	FMC_SDCKE0	-	-	EVENTOUT
	PC6	-	-	TIM3_CH1	TIM8_CH1	-	I2S2_MCK	-	DFSDM1_CKIN3	USART6_TX	FMC_NWAIT	SDMMC2_D6	-	SDMMC_D6	DCMI_D0	LCD_HSYNC	EVENTOUT
	PC7	-	-	TIM3_CH2	TIM8_CH2	-	-	I2S3_MCK	DFSDM1_DATAIN3	USART6_RX	FMC_NE1	SDMMC2_D7	-	SDMMC_D7	DCMI_D1	LCD_G6	EVENTOUT
	PC8	TRACED1	-	TIM3_CH3	TIM8_CH3	-	-	-	UART5_RTS	USART6_CK	FMC_NE2/FMC_NCE	-	-	SDMMC_D0	DCMI_D2	-	EVENTOUT
	PC9	MCO2	-	TIM3_CH4	TIM8_CH4	I2C3_SDA	I2S_CKIN	-	UART5_CTS	-	QUADSPI_BK1_IO0	LCD_G3	-	SDMMC_D1	DCMI_D3	LCD_B2	EVENTOUT
	PC10	-	-	-	DFSDM1_CKIN5	-	-	SPI3_SCK/I2S3_CK	USART3_TX	UART4_TX	QUADSPI_BK1_IO1	-	-	SDMMC_D2	DCMI_D8	LCD_R2	EVENTOUT

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 33. Typical and maximum current consumption in Sleep mode, regulator ON

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Sleep mode	All peripherals enabled(2)	216	128	144(3)	190(3)	-	mA
			200	119	134	180	214	
			180	105	118(3)	153(3)	178(3)	
			168	93	105	136	156	
			144	72	80	107	124	
			60	33	39	65	82	
			25	17	21	47	65	
		All peripherals disabled	216	18	25(3)	71(3)	-	
			200	17	24	70	112	
			180	14	20(3)	54(3)	75(3)	
			168	13	18	49	69	
			144	10	14	40	58	
			60	6	10	36	53	
			25	4	8	34	51	

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. Guaranteed by test in production.

Figure 36. MIPI D-PHY HS/LP clock lane transition timing diagram

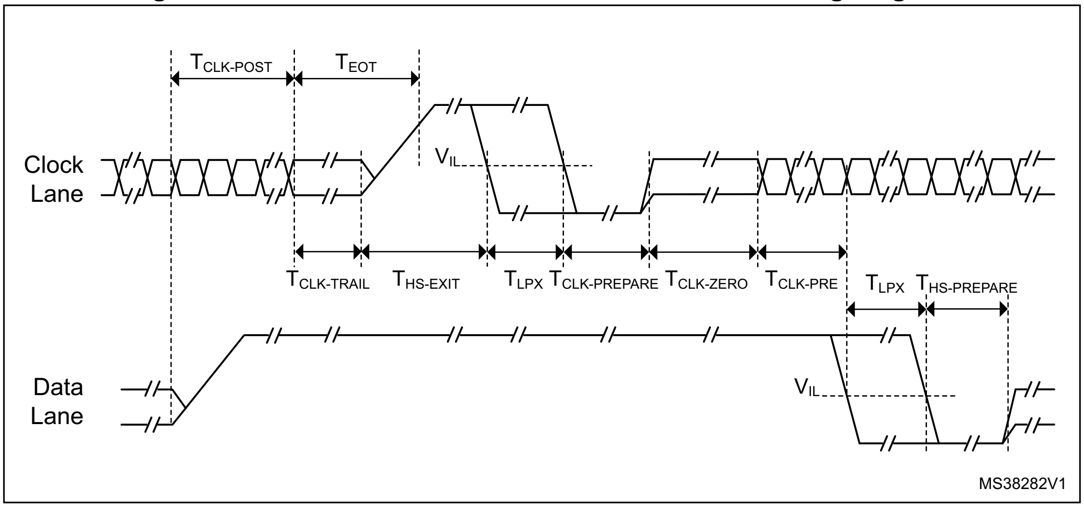
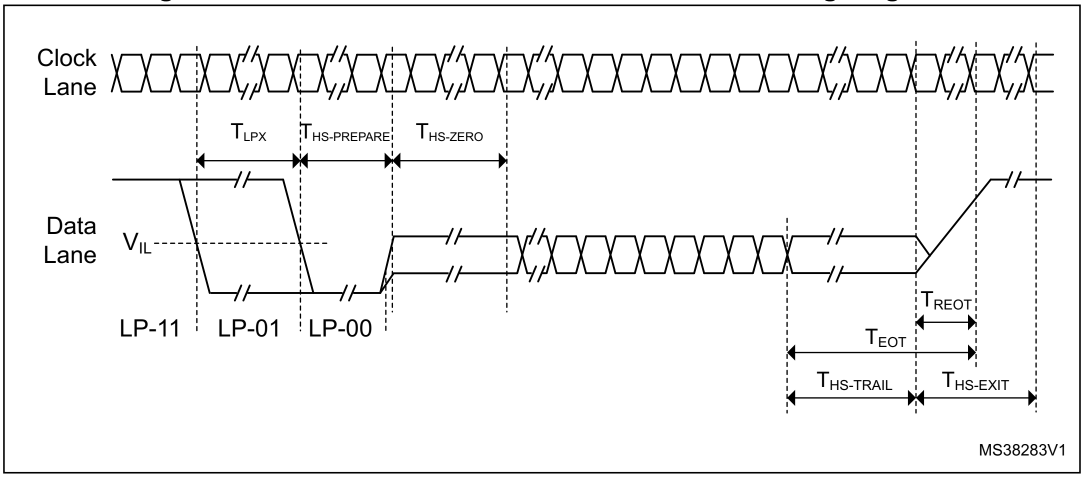


Figure 37. MIPI D-PHY HS/LP data lane transition timing diagram



5.3.14 MIPI D-PHY PLL characteristics

The parameters given in *Table 53* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 53. DSI-PLL characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock	-	4	-	100	MHz
f_{PLL_INFIN}	PFD input clock	-	4	-	25	MHz
f_{PLL_OUT}	PLL multiplier output clock	-	31.25	-	500	MHz
f_{VCO_OUT}	PLL VCO output	-	500	-	1000	MHz
t_{LOCK}	PLL lock time	-	-	-	200	µs

Table 53. DSI-PLL characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(PLL)}$	PLL power consumption on V_{DD12}	f_{VCO_OUT} = 500 MHz	-	0.55	0.70	mA
		f_{VCO_OUT} = 600 MHz	-	0.65	0.80	
		f_{VCO_OUT} = 1000 MHz	-	0.95	1.20	

1. Based on test during characterization.

5.3.15 MIPI D-PHY regulator characteristics

The parameters given in *Table 54* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 54. DSI regulator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DD12DSI}$	1.2 V internal voltage on $V_{DD12DSI}$	-	1.15	1.20	1.30	V
C_{EXT}	External capacitor on V_{CAPDSI}	-	1.1	2.2	3.3	µF
ESR	External Serial Resistor	-	0	25	600	mΩ
$I_{DDDSIREG}$	Regulator power consumption	-	100	120	125	µA
I_{DDDSI}	DSI system (regulator, PLL and D-PHY) current consumption on V_{DDDSI}	Ultra Low Power Mode (Reg. ON + PLL OFF)	-	290	600	µA
		Stop State (Reg. ON + PLL OFF)	-	290	600	
$I_{DDDSILP}$	DSI system current consumption on V_{DDDSI} in LP mode communication(2)	10 MHz escape clock (Reg. ON + PLL OFF)	-	4.3	5.0	mA
		20 MHz escape clock (Reg. ON + PLL OFF)	-	4.3	5.0	
$I_{DDDSIHS}$	DSI system (regulator, PLL and D-PHY) current consumption on V_{DDDSI} in HS mode communication(3)	300 Mbps - 1 data lane (Reg. ON + PLL ON)	-	8.0	8.8	mA
		300 Mbps - 2data lane (Reg. ON + PLL ON)	-	11.4	12.5	
		500 Mbps - 1 data lane (Reg. ON + PLL ON)	-	13.5	14.7	
		500 Mbps - 2data lane (Reg. ON + PLL ON)	-	18.0	19.6	
	DSI system (regulator, PLL and D-PHY) current consumption on V_{DDDSI} in HS mode with CLK like payload	500 Mbps - 2data lane (Reg. ON + PLL ON)	-	21.4	23.3	
t_{WAKEUP}	Startup delay	C_{EXT} = 2.2 µF	-	110	-	µs
		C_{EXT} = 3.3 µF	-	-	160	
I_{INRUSH}	Inrush current on V_{DDDSI}	External capacitor load at start	-	60	200	mA

1. Based on test during characterization.
2. Values based on an average traffic in LP Command Mode.
3. Values based on an average traffic (3/4 HS traffic & 1/4 LP) in Video Mode.

Table 62. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C conforming to ANSI/ESDA/JEDEC JS-001-2012	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C conforming to ANSI/ESD S5.3.1-2009, all the packages	3	250	V

1. Guaranteed by characterization results.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 63. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

5.3.19 I/O current injection characteristics

As a general rule, a current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during the normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when an abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during the device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset, oscillator frequency deviation).

A negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in *Table 64*.

Unless otherwise specified, the parameters given in *Table 67* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 67. I/O AC characteristics(1)(2)

OSPEEDRy [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} ≥ 2.7 V	-	-	4	MHz
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	2	
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	8	
			C_L = 10 pF, V_{DD} ≥ 1.8 V	-	-	4	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	3	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} = 1.7 V to 3.6 V	-	-	100	ns
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD}≥ 2.7 V	-	-	25	MHz
			C_L = 50 pF, V_{DD}≥ 1.8 V	-	-	12.5	
			C_L = 50 pF, V_{DD}≥ 1.7 V	-	-	10	
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	50	
			C_L = 10 pF, V_{DD}≥ 1.8 V	-	-	20	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	12.5	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} ≥ 2.7 V	-	-	10	ns
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	6	
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	20	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	10	
10	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 40 pF, V_{DD} ≥ 2.7 V	-	-	50(4)	MHz
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	100(4)	
			C_L = 40 pF, V_{DD} ≥ 1.7 V	-	-	25	
			C_L = 10 pF, V_{DD} ≥ 1.8 V	-	-	50	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	42.5	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 40 pF, V_{DD} ≥2.7 V	-	-	6	ns
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	4	
			C_L = 40 pF, V_{DD} ≥ 1.7 V	-	-	10	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	6	

I^2S interface characteristics

Unless otherwise specified, the parameters given in Table 86 for the I^2S interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in Table 17, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to Section 5.3.20: I/O port characteristics for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 86. I^2S dynamic characteristics[1]

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256x8K	256xFs[2]	MHz
f_{CK}	I2S clock frequency	Master data	-	64xFs	MHz
		Slave data	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	-	3	ns
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	5	-	
$t_{h(WS)}$	WS hold time	Slave mode	2	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	2.5	-	
$t_{su(SD\_SR)}$		Slave receiver	2.5	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	3.5	-	
$t_{h(SD\_SR)}$		Slave receiver	2	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	12	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	3	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	5	-	
$t_{h(SD\_MT)}$		Master transmitter (after enable edge)	0	-	

1. Guaranteed by characterization results.
2. The maximum value of 256xFs is 49.152 MHz (APB1 maximum frequency).

*Note: Refer to RM0410 reference manual I2S section for more details about the sampling frequency (F_S). f_{MCK}, f_{CK}, and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of (I2SDIV/(2*I2SDIV+ODD) and a maximum value of (I2SDIV+ODD)/(2*I2SDIV+ODD). F_S maximum value is supported for each mode/condition.*

JATG/SWD characteristics

Unless otherwise specified, the parameters given in *Table 87* for JTAG/SWD are derived from tests performed under the ambient temperature, f_{HCLK} frequency and VDD supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C=30 pF
- Measurement points are performed at CMOS levels: $0.5V_{DD}$

Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output alternate function characteristics (SCK,SD,WS).

Table 87. Dynamics characteristics: JTAG characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
F_{pp}	TCK clock frequency	2.7V <VDD< 3.6V	-	-	40	MHz
$1/t_{c(TCK)}$		1.71 <VDD< 3.6V	-	-	35	
$t_{w(TCKH)}$	SCK high and low time	-	$T_{PCLK} - 1$	T_{PCLK}	$T_{PCLK} + 1$	ns
$t_{w(TCKL)}$						
$t_{su(TMS)}$	TMS input setup time	-	3	-	-	
$t_{h(TMS)}$	TMS input hold time	-	0	-	-	
$t_{su(TDI)}$	TDI input setup time	-	0.5	-	-	
$t_{h(TDI)}$	TDI input hold time	-	2	-	-	
$t_{ov (TDO)}$	TDO output valid time	2.7V <VDD< 3.6V	-	9	11	
		1.71 <VDD< 3.6V	-	9	13	
$t_{oh(TDO)}$	TDO output hold time	-	7.5	-	-	

Table 104. Asynchronous multiplexed PSRAM/NOR read timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK} - 1$	$3T_{HCLK} + 1$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK}$	$2T_{HCLK} + 0.5$	
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK} - 1$	$T_{HCLK} + 1$	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0.5	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	0.5	
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK} - 0.5$	$T_{HCLK}+1$	
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high)	$T_{HCLK} + 0.5$	-	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK} - 0.5$	-	
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK} - 1$	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK} - 1$	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	

1. Guaranteed by characterization results.

Table 105. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK} - 1$	$8T_{HCLK} + 1$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1.5$	$5T_{HCLK} + 0.5$	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK} + 1.5$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+ 1$	-	

1. Guaranteed by characterization results.

Figure 74. SDRAM write access waveforms

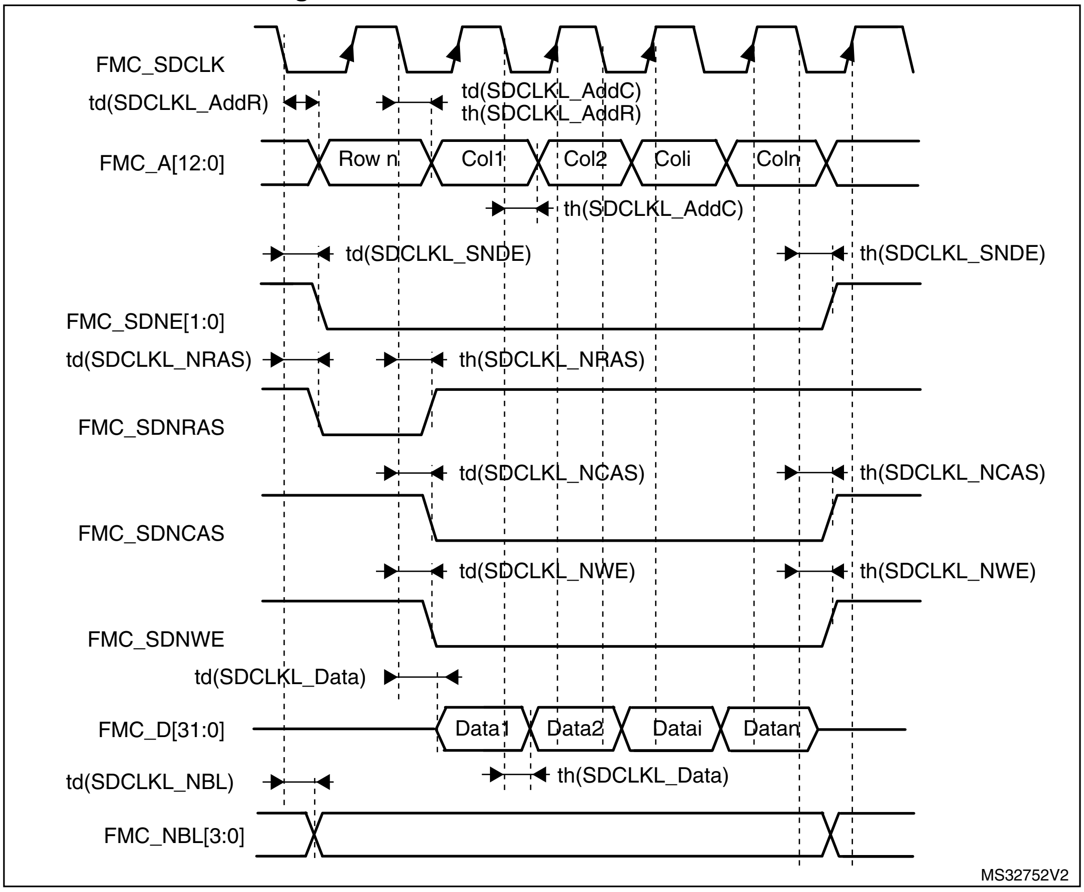


Table 116. SDRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 0.5$	ns
$t_{d(SDCLKL\_Data)}$	Data output valid time	-	3	
$t_{h(SDCLKL\_Data)}$	Data output hold time	0	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	3.5	
$t_{d(SDCLKL\_SDNWE)}$	SDNWE valid time	-	1.5	
$t_{h(SDCLKL\_SDNWE)}$	SDNWE hold time	0.5	-	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	1.5	
$t_{h(SDCLKL-\_SDNE)}$	Chip select hold time	0.5	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	1	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0.5	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	1	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0.5	-	

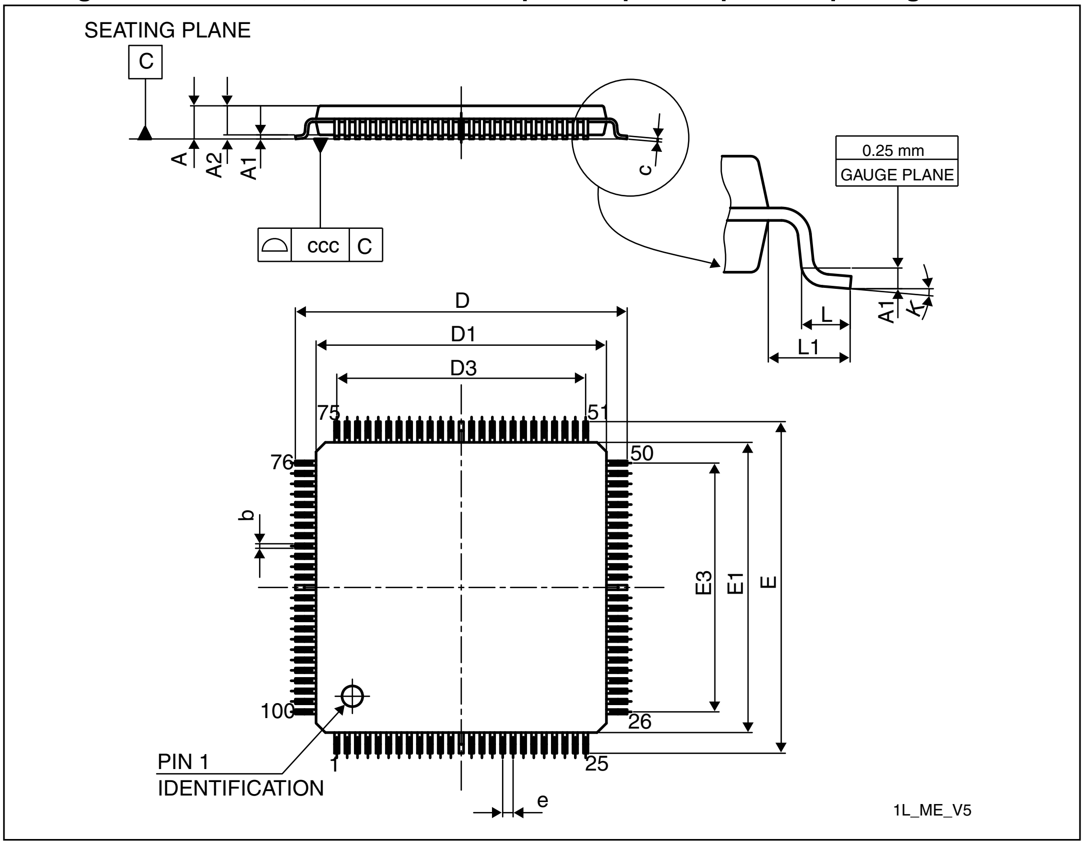
1. Guaranteed by characterization results.

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

6.1 LQFP100 14x 14 mm, low-profile quad flat package information

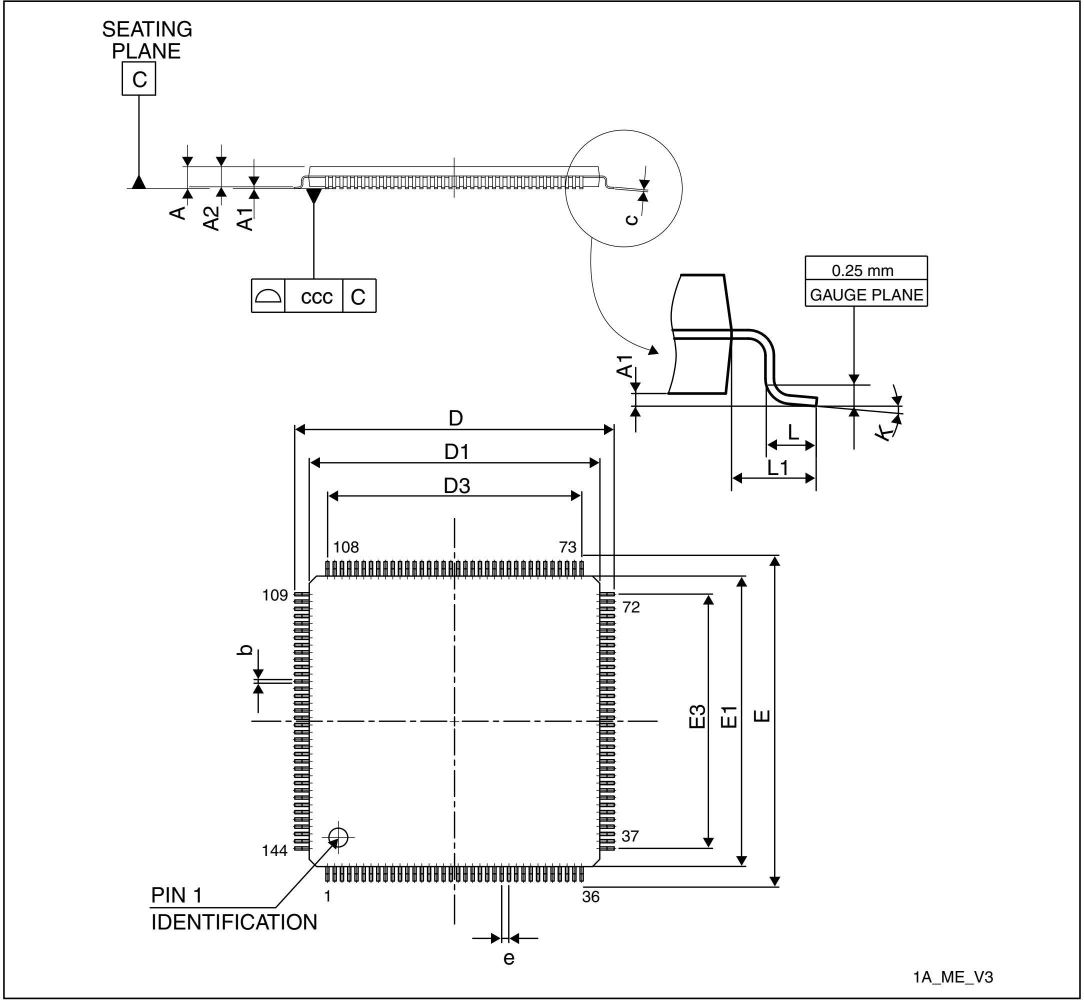
Figure 83. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline



1. Drawing is not to scale.

6.2 LQFP144 20 x 20 mm, low-profile quad flat package information

Figure 86. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 129. WLCSP 180-bump, 5.5 x 6 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3	-	0.025	-	-	0.0010	-
b(2)	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	5.502	5.537	5.572	0.2166	0.2180	0.2194
E	6.060	6.095	6.130	0.2386	0.2400	0.2413
e	-	0.400	-	-	0.0157	-
e1	-	4.800	-	-	0.1890	-
e2	-	5.200	-	-	0.2047	-
F	-	0.368	-	-	0.0145	-
G	-	0.477	-	-	0.0188	-
aaa	-	0.110	-	-	0.0043	-
bbb	-	0.110	-	-	0.0043	-
ccc	-	0.110	-	-	0.0043	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.